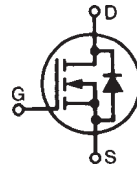


HiPerFET™ Power MOSFET Q2-Class

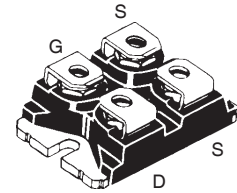
IXFN70N60Q2

$V_{DSS} = 600V$
 $I_{D25} = 70A$
 $R_{DS(on)} \leq 88m\Omega$
 $t_{rr} \leq 250ns$



N-Channel Enhancement Mode
 Avalanche Rated, Low Q_g , Low Intrinsic R_g
 High dV/dt , Low t_{rr}

miniBLOC, SOT-227 B
 E153432



G = Gate D = Drain
 S = Source

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	600	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	70	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	280	A
I_A	$T_C = 25^\circ C$	70	A
E_{AS}	$T_C = 25^\circ C$	5	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	20	V/ns
P_D	$T_C = 25^\circ C$	890	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
V_{ISOL}	50/60Hz, RMS $t = 1min$	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1s$	3000	V~
M_d	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
Weight		30	g

Features

- Double Metal Process for Low Gate Resistance
- miniBLOC, with Aluminium Nitride Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier

Applications

- DC-DC Converters
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Pulse Generators

Advantages

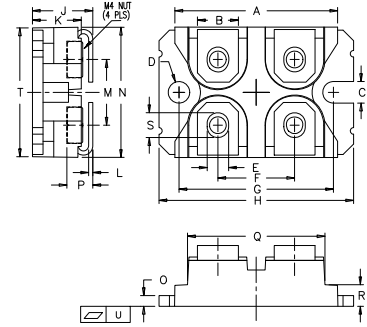
- Easy to Mount
- Space Savings
- High Power Density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8mA$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$			50 μA
	$T_J = 125^\circ C$			3 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			88 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	36	50	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		12	nF
C_{oss}			1340	pF
C_{rss}			345	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 35\text{A}$ $R_G = 1\Omega$ (External)		26	ns
t_r			25	ns
$t_{d(off)}$			60	ns
t_f			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		265	nC
Q_{gs}			57	nC
Q_{gd}			120	nC
R_{thJC}			0.14	$^\circ\text{C/W}$
R_{thCS}		0.05		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			70 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			280 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 25\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$			250 ns
Q_{RM}			1.2	μC
I_{RM}			8.0	A

SOT-227B Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Notes1: Pulse Test, $t \leq 300\mu\text{s}$; Duty Cycle, $d \leq 2\%$.

Ordering Information

The IXFN70N60Q2 is also available with brass capture nuts in place of the normal Zinc coated steel capture nuts. The ordering part number is IXFN70N60Q2-BN.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

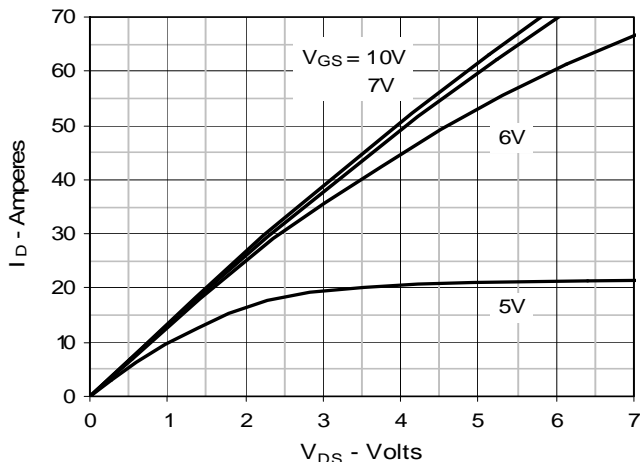
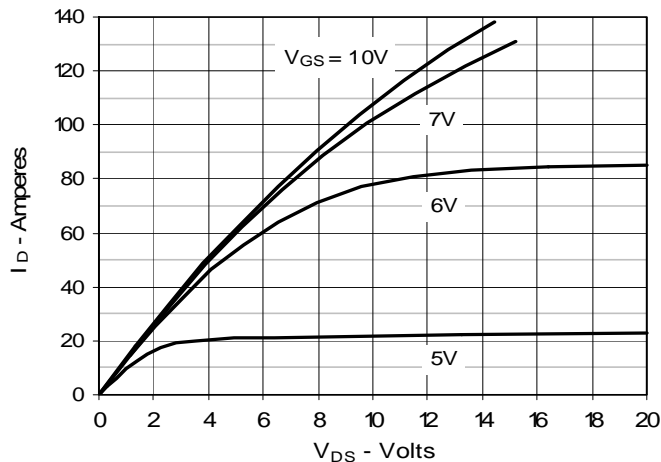
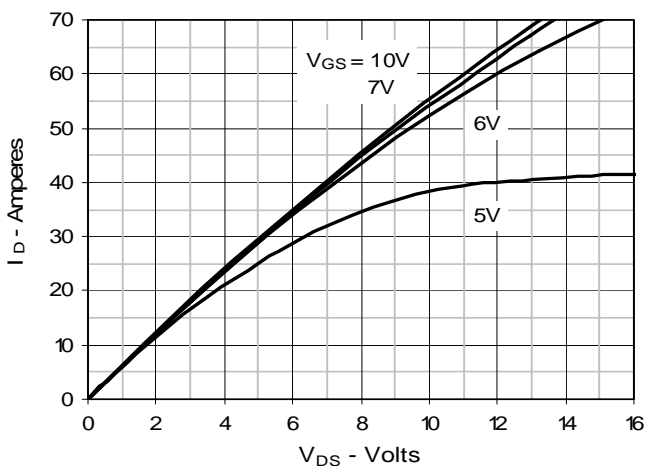
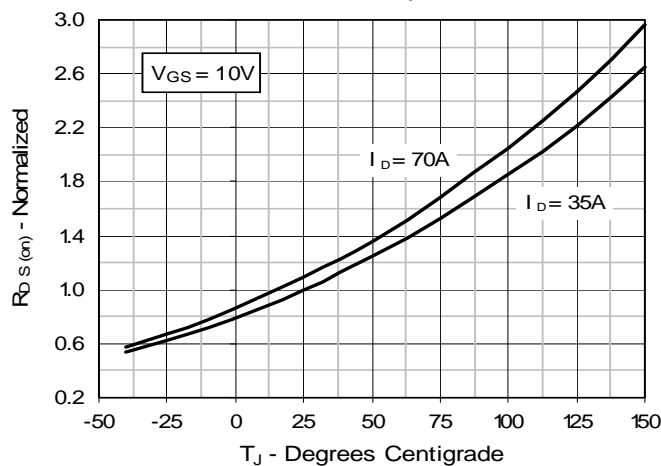
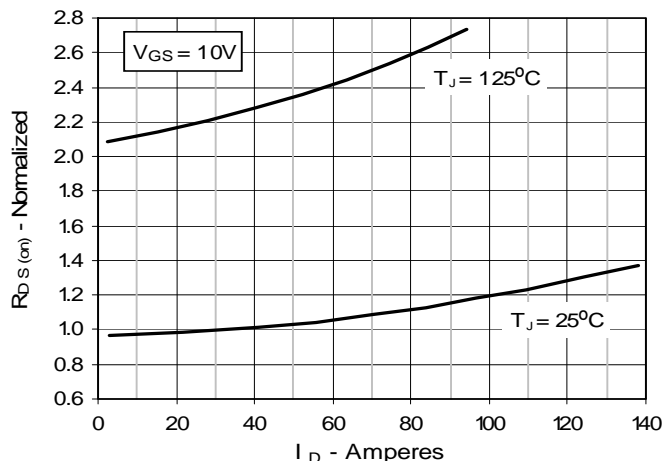
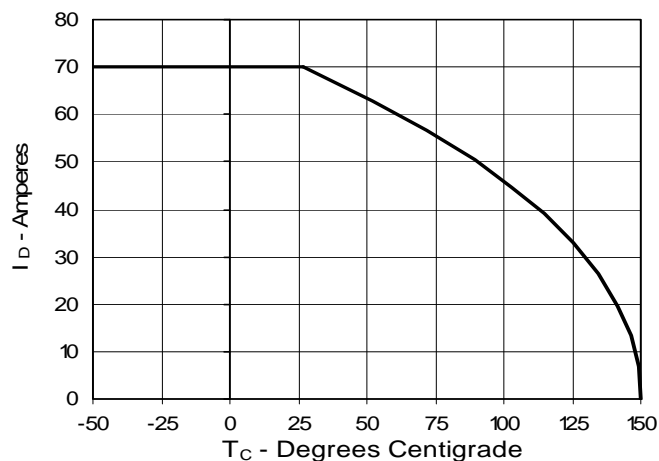
Fig. 1. Output Characteristics
 @ 25°C

Fig. 2. Extended Output Characteristics
 @ 25°C

Fig. 3. Output Characteristics
 @ 125°C

Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

Fig. 6. Drain Current vs. Case Temperature


Fig. 7. Input Admittance

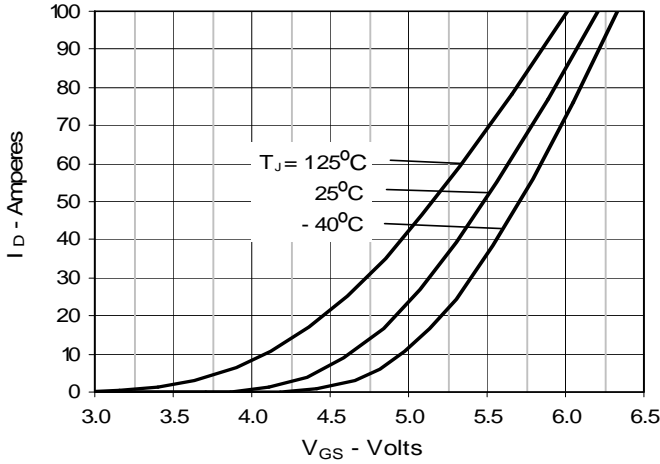


Fig. 8. Transconductance

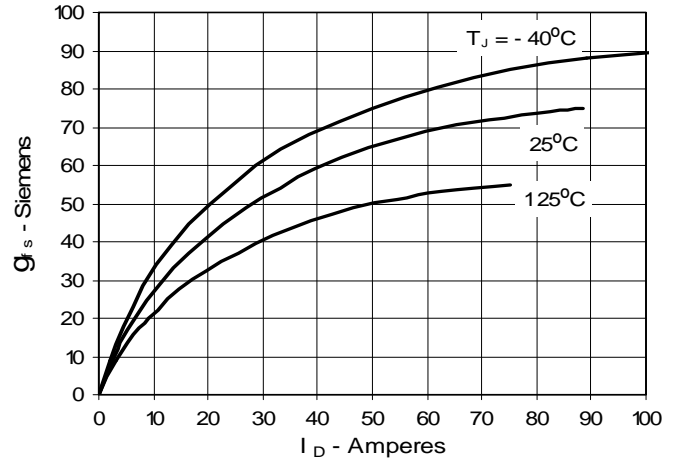


Fig. 9. Source Current vs. Source-To-Drain Voltage

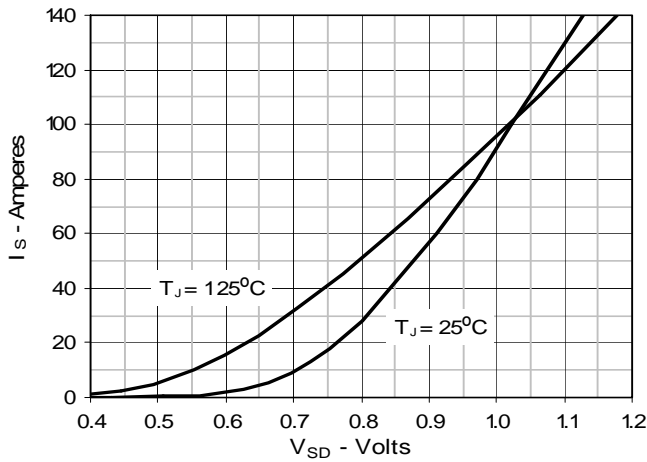


Fig. 10. Gate Charge

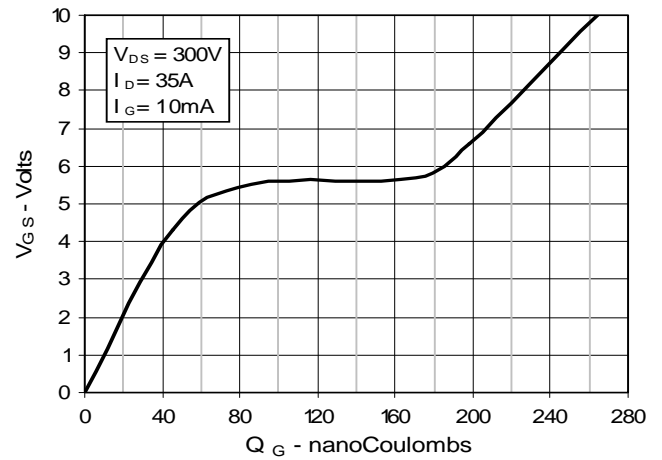


Fig. 11. Capacitance

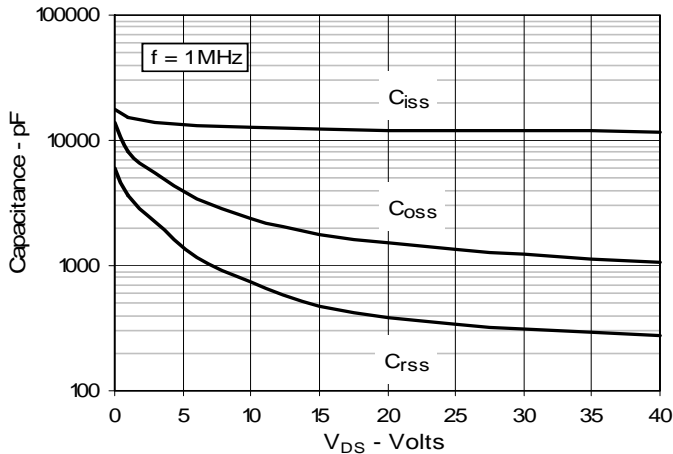


Fig. 12. Maximum Transient Thermal Impedance

